



**ABSOLUTE MAXIMUM RATINGS**

Input Supply Voltage, (+VIN,+Vc) . . . . .	20V
UV Comparator, and Digital Inputs	
Maximum forced voltage . . . . .	-0.3V to 10V
Maximum forced current . . . . .	±10mA
C/S Inputs	
Maximum forced voltage . . . . .	-0.3V to 20V
A and B Amplifier Inputs . . . . .	-0.3V to +VIN
Open Collector Output Voltages. . . . .	20V
A and B Output Currents (continuous)	
Source . . . . .	Internally Limited
Sink . . . . .	1.0A
Parking Drive Output Current	
Continuous . . . . .	150mA
Pulsed . . . . .	1A
Output Diode Current (pulsed) . . . . .	1A
Power OK Output Current(continuous) . . . . .	30mA
Operating Junction Temperature . . . . .	-55°C to +150°C
Storage Temperature . . . . .	-65°C to +150°C

Note 1: Unless otherwise indicated, voltages are referenced to ground and currents are positive into, negative out of, the specified terminals.

"Pulsed" is defined as a less than 10% duty cycle pulse with a maximum duration of 500 $\mu$ s.

Note 2: See Unitrode Integrated Circuits databook for information regarding thermal specifications and limitations of packages.

**Thermal Data****QP Package:**

Thermal Resistance Junction to Leads,

$\theta_{JL}$  . . . . . 15°C/W

Thermal Resistance Junction to Ambient,

$\theta_{JA}$  . . . . . 40°C/W

**CONNECTION DIAGRAMS**

SOIC-24 (Top View) DW Package		PLCC-28 (Top View) QP Package		PACKAGE PIN FUNCTION	
				FUNCTION	PIN
+VIN	1			+VIN	1
INH	2			INH	2
UV2	3			UV2	3
UV1	4			UV1	4
Limit	5			Limit	5
Park Volts	6			Park Volts	6
C/S-	7			C/S-	7
A+/REF Input	8			A+/REF Input	8
A- In	9			A- In	9
A Output	10			A Output	10
A Output	11			A Cur Sen	11
A Cur Sen	12			Gnd (Heat Dissipation Pins)	12-18
				B Cur Sen	19
				B Output	20
				+Vc Supply	21
				B- In	22
				B+ In	23
				C/S+	24
				Pwr OK	25
				Park	26
				Park Drive	27
				C/S Out	28

**ELECTRICAL CHARACTERISTICS:** Unless otherwise stated specifications apply for 0°C ≤ TA ≤ 70°C, +VIN = 12V, +Vc = +VIN, A+/REF Input = 6V. TA=TJ.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNITS
<b>INPUT SUPPLY</b>					
+VIN Supply Current	All Amplifier Outputs = 6V		35	42	mA
+Vc Supply Current	IOUT = 0A		1		mA
+VIN UVLO Threshold	Low to High		2.8	3.0	V
UVLO Threshold Hysteresis			200		mV

**ELECTRICAL  
CHARACTERISTICS (cont.)**

Unless otherwise stated specifications apply for  $0^{\circ}\text{C} \leq T_A \leq 70^{\circ}\text{C}$ ,  $+V_{IN} = 12\text{V}$ ,  $+V_C = +V_{IN}$ ,  
 $A+/REF \text{ INPUT} = 6\text{V}$ .  $T_A = T_J$ .

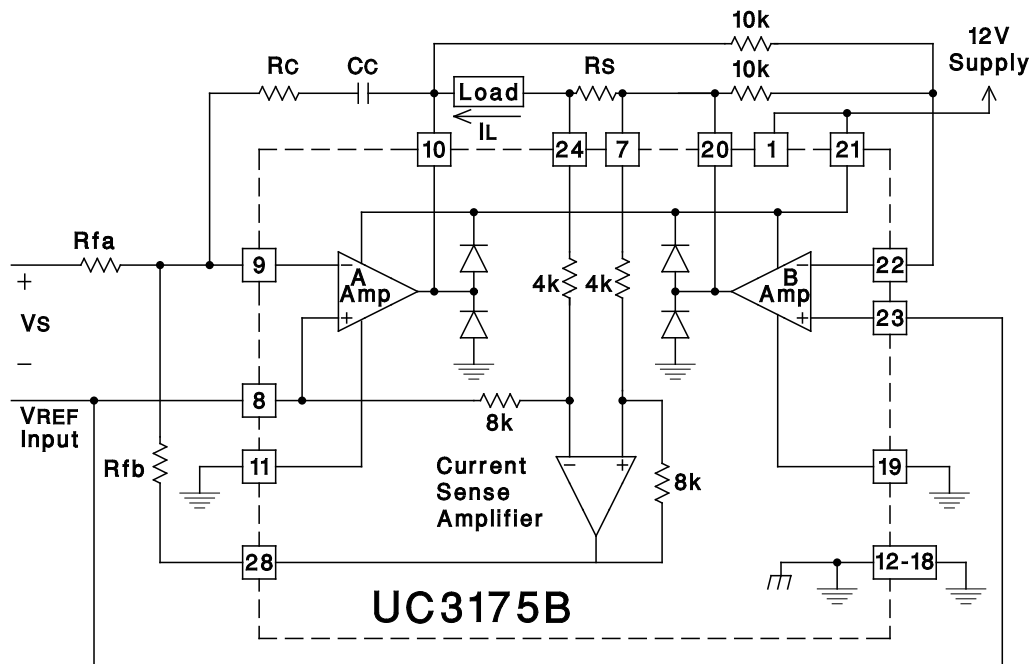
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNITS
<b>UNDER VOLTAGE (UV) COMPARATOR</b>					
Input Bias Current		-1.5	-0.5		$\mu\text{A}$
UV Thresholds	Low to High, Other Input = 5V	1.48	1.50	1.52	V
UV Threshold Hysteresis		15	25	40	mV
Pwr OK $V_{SAT}$	$I_{OUT} = 5\text{mA}$			0.45	V
Pwr OK Leakage	$V_{OUT} = 20\text{V}$			5	$\mu\text{A}$
<b>POWER AMPLIFIERS A and B</b>					
Input Offset Voltage	$V_{CM} = 6\text{V}$ , A Amplifier			8	mV
	B Amplifier			12	mV
Input Offset Drift	Note 1, A Amplifier Only			25	$\mu\text{V}/^{\circ}\text{C}$
Input Bias Current	$V_{CM} = 6\text{V}$ , except A+/REF Input	-500	-150		nA
Input Offset Current	$V_{CM} = 6\text{V}$ , B Amplifier Only			200	nA
Input Bias Current at A+/Ref Input	$(A+/Ref-C/S+)/12k$ , $T_J = 25^{\circ}\text{C}$	60	84	105	$\mu\text{A}/\text{V}$
CMRR	$1\text{V} \leq V_{CM} \leq 10\text{V}$	70	90		dB
PSRR	$+V_{IN} = 4\text{V}$ to $15\text{V}$ , $V_{CM} = 1.5\text{V}$	70	90		dB
Large Signal Voltage Gain	$V_{OUT} = 1\text{V}$ , Sinking 500mA to $V_{OUT} = 11\text{V}$ , Sourcing 500mA	3.0	15.0		V/mV
Slew Rate	1 to 13V, 13 to 1V, $T_J = 25^{\circ}\text{C}$		1	2.1	V/ $\mu\text{s}$
Unity Gain Bandwidth	Note 1, A Amplifier		2		MHz
	Note 1, B Amplifier		1		MHz
High-Side Current Limit		0.8	1.0		A
Output Saturation Voltage	High-Side, $I_{SOURCE} = 250\text{mA}$		0.7		V
	High-Side, $I_{SOURCE} = 800\text{mA}$		0.85		V
	Low-Side, $I_{SINK} = 250\text{mA}$		0.3		V
	Low-Side, $I_{SINK} = 800\text{mA}$		0.4		V
	Total, $I_{OUT} = 250\text{mA}$		1.0	1.2	V
	Total, $I_{OUT} = 800\text{mA}$		1.25	1.6	V
High Side Diode $V_F$	$I_D = 800\text{mA}$ , Inhibit Activated		1.0		V
Low Side Diode $V_F$	$I_D = 800\text{mA}$ , Inhibit Activated		1.0		V
<b>CURRENT SENSE AMPLIFIER</b>					
Input Offset Voltage	$V_{CM} = 6\text{V}$			2.0	mV
Input Offset Change with Common Mode Input	$0\text{V} \leq V_{CM} \leq 12\text{V}$			1500	$\mu\text{V}/\text{V}$
Input Offset Drift	Note 1			8	$\mu\text{V}/^{\circ}\text{C}$
Voltage Gain	$-1.0\text{V} \leq V_{DIFF} \leq +1.0\text{V}$ , $V_{CM} = 6\text{V}$	1.95	2.00	2.05	V
Output Saturation Voltage	Low-Side, $I_{SINK} = 1.5\text{mA}$		0.3	0.5	V
	High-Side, $I_{SOURCE} = 1.5\text{mA}$		0.4	0.7	V
Maximum A+/Ref Input	Volts Below $+V_{IN}$ , C/S+ & C/S- = BOUTPUT Max @ 10mA Output Current, $+V_{IN} = 4.5\text{V}$ , C/S VIO $\leq 5\text{mV}$		2.6	3.0	V
<b>PARKING FUNCTION</b>					
Park Input Threshold		0.7	1.1	1.7	V
Park Input Current	Park Input = 1.7V		60	100	$\mu\text{A}$
Park Drive Saturation Voltage, $PD_{VSAT}$	$I_{SINK} = 100\text{mA}$		0.3	0.5	V
Parking Drive Leakage	$V_{OUT} = 20\text{V}$			100	$\mu\text{A}$
Amplifier A Aux Input Bias Current		-500	-150		nA

**ELECTRICAL  
CHARACTERISTICS (cont.)**

Unless otherwise stated specifications apply for  $0^{\circ}\text{C} \leq T_A \leq 70^{\circ}\text{C}$ ,  $+V_{\text{IN}} = 12\text{V}$ ,  $+V_{\text{C}} = +V_{\text{IN}}$ ,  
 $A+/\text{REF}$  Input = 6V.  $T_A = T_J$ .

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNITS
<b>PARKING FUNCTIONS (cont.)</b>					
Amplifier A Saturation Voltage, $A_{\text{HVSAT}}$	$I_{\text{SOURCE}} = 50\text{mA}$ , $+V_{\text{IN}} = 3\text{V}$		0.65	0.8	V
Regulating Voltage at Park Volts		1.47	1.50	1.53	V
Minimum Parking Supply Voltage	$A_{\text{HVSAT}} + P_{\text{DVSAT}} \leq 1.3\text{V}$ @ 50mA		1.7	1.9	V
<b>AUXILIARY FUNCTIONS</b>					
Limit Input Low Voltage	A Output Forced Low	0.7	0.8		V
Limit Input High Voltage	A Output Forced High		2.2	2.3	V
Limit Inactive		1.2		1.8	V
Limit Open Circuit Voltage		1.45	1.50	1.55	V
Limit Input Resistance	$1.2\text{V} \leq \text{Limit Input} \leq 1.8\text{V}$		10		$\text{k}\Omega$
Inhibit Input Threshold		0.7	1.1	1.7	V
Inhibit Input Current	Inhibit Input = 1.7V		400	700	$\mu\text{A}$
Supply Current when Inhibited	The sum of $+V_{\text{IN}}$ and $+V_{\text{C}}$ currents		2	6	mA
Thermal Shutdown Temperature			165		$^{\circ}\text{C}$

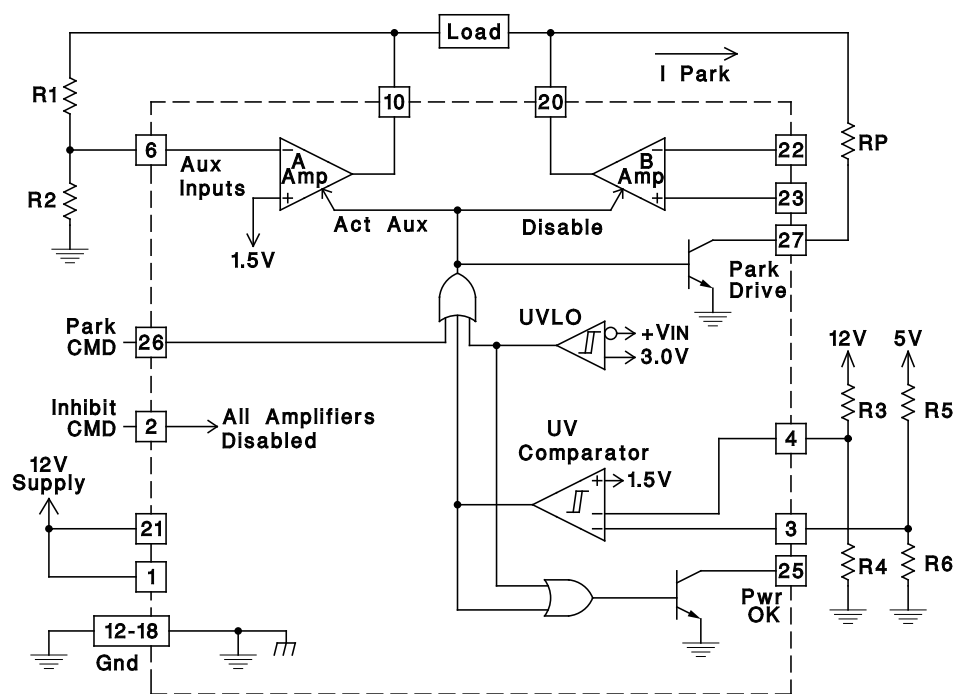
Note 1: This specification not tested in production.

**UC3175B Series Current Sensing**

UDG-92058

$$G_o = \frac{I_L}{V_s} = \frac{R_{fb}}{R_{fa} \cdot 2 \cdot R_s}$$

## Parking Function



UDG-92059

Notes:  $\text{Parking voltage} = \frac{1.5V \cdot R1 + R2}{R2 - (IL \cdot RP)}$   
 RP is optional for current limiting.  
 Inhibit and Park Inputs are active high.  
 Pwr OK is low on power failure.

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